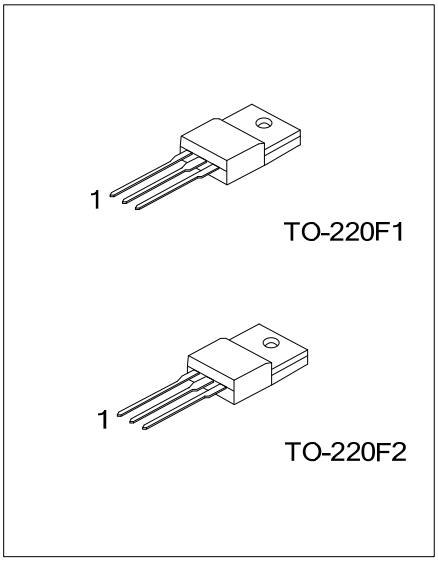
20N70-HC

Power MOSFET

20A, 700V N-CHANNEL POWER MOSFET



■ DESCRIPTION

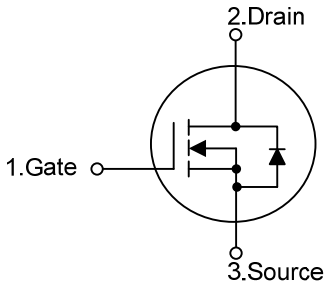
The UTC **20N70-HC** is a N-channel enhancement MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$, high switching speed, high current capacity and low gate charge.

The UTC **20N70-HC** is universally applied in low voltage such as automotive, high efficiency switching for AC/DC converters and DC motor control, etc.

■ FEATURES

* $R_{DS(ON)} \leq 0.42\ \Omega$ @ V_{GS}=10V, I_D=10A
* High Switching Speed

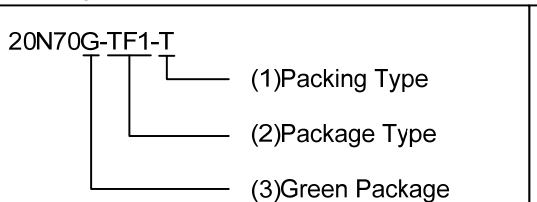
■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
20N70L-TF1-T	20N70G-TF1-T	TO-220F1	G	D	S	Tube
20N70L-TF2-T	20N70G-TF2-T	TO-220F2	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

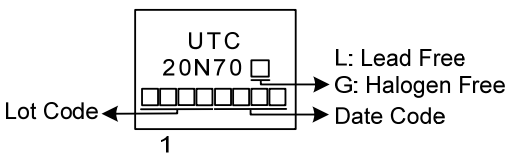


(1) T: Tube

(2) TF1: TO-220F1, TF2: TO-220F2

(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Current	Continuous	I_D	20	A
	Pulsed	I_{DM}	40	A
Single Pulsed Avalanche Energy		E_{AS}	821	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.9	V/ns
Power Dissipation		P_D	45	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating : Pulse width limited by maximum junction temperature.
3. L=30mH, I_{AS}=7.4A, V_{DD}=50V, R_G=25Ω, Starting T_J = 25°C
4. I_{SD}≤20A, di/dt≤200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

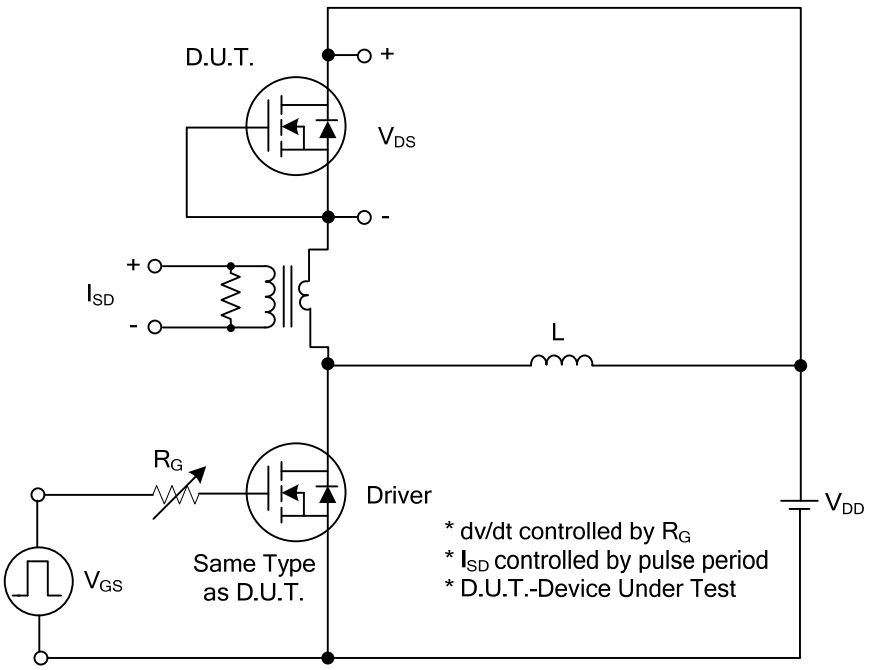
PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	θ_{JA}	62.5	°C/W
Junction to Case	θ_{JC}	2.7	°C/W

■ ELECTRICAL CHARACTERISTICS

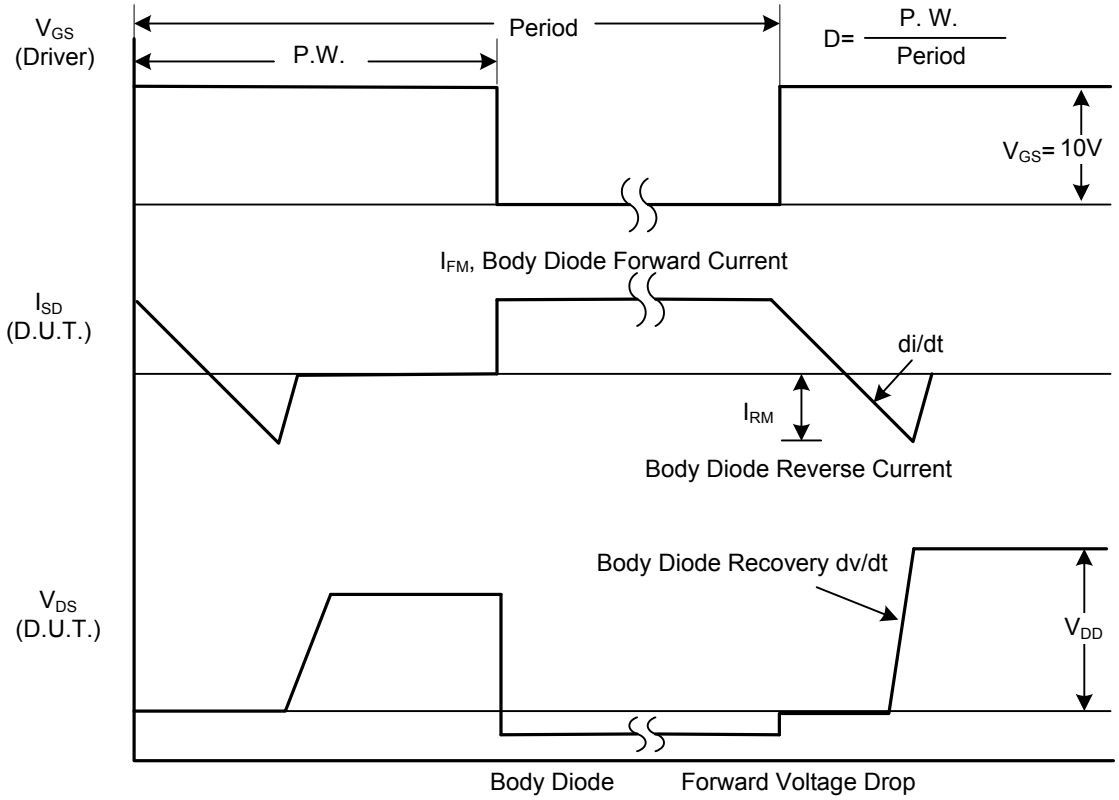
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V	700			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=700V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=10A			0.42	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		3150		pF
Output Capacitance		C_{OSS}			285		pF
Reverse Transfer Capacitance		C_{RSS}			29		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=560V, V_{GS}=10V, I_D=20A I_G=1mA (Note 1, 2)		89		nC
Gate to Source Charge		Q_{GS}			19		nC
Gate to Drain Charge		Q_{GD}			31		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=100V, V_{GS}=10V, I_D=20A, R_G=25Ω (Note 1, 2)		35		ns
Rise Time		t_R			32		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			280		ns
Fall-Time		t_F			80		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				20	A
Maximum Body-Diode Pulsed Current		I_{SM}				40	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=20A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time		t_{rr}	I_S=20A, V_{GS}=0V, dI_F/dt=100A/μs (Note 1)		500		ns
Reverse Recovery Charge		Q_{rr}			9.2		μC

Notes: 1. Pulse Test: Pulse width ≤ 700μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

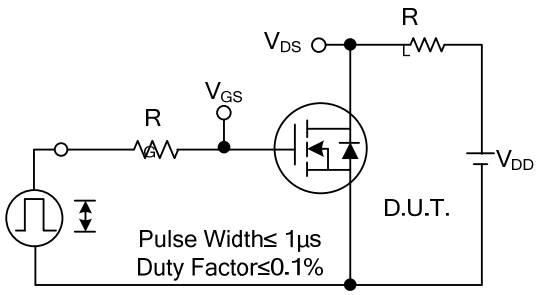


Peak Diode Recovery dv/dt Test Circuit

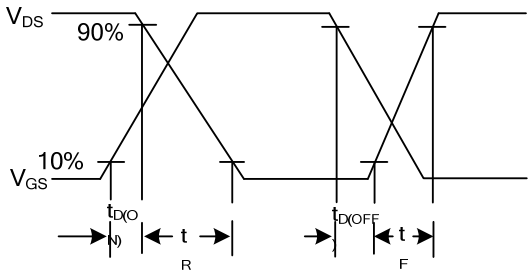


Peak Diode Recovery dv/dt Waveforms

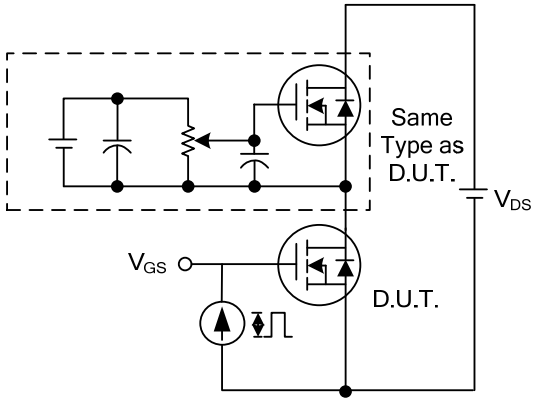
■ TEST CIRCUITS AND WAVEFORMS



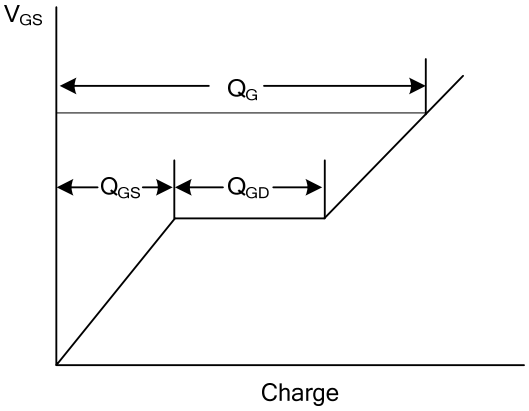
Switching Test Circuit



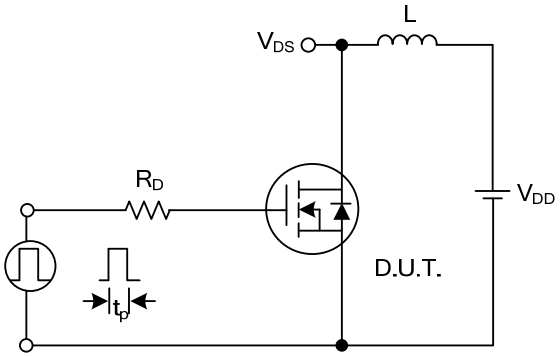
Switching Waveforms



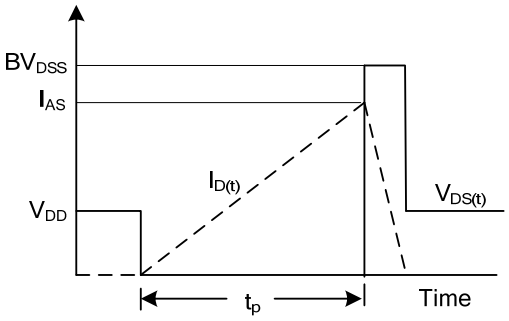
Gate Charge Test Circuit



Gate Charge Waveform



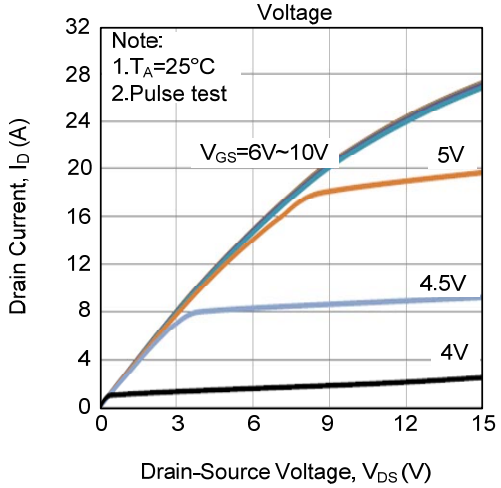
Unclamped Inductive Switching Test Circuit



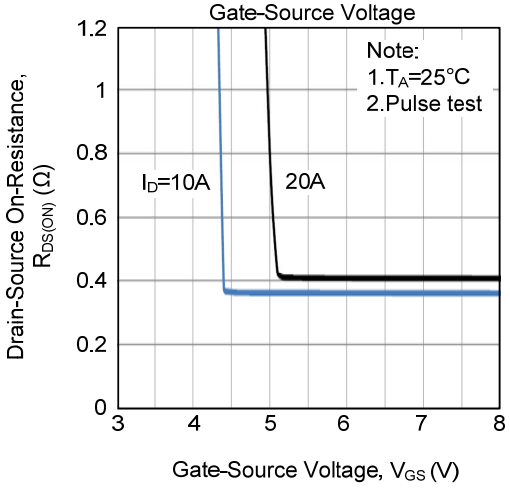
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

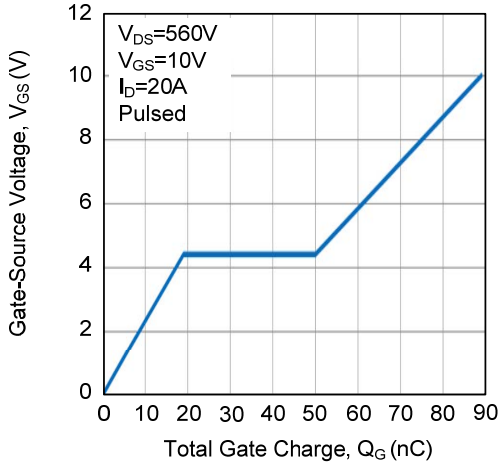
Drain Current vs. Drain-Source Voltage



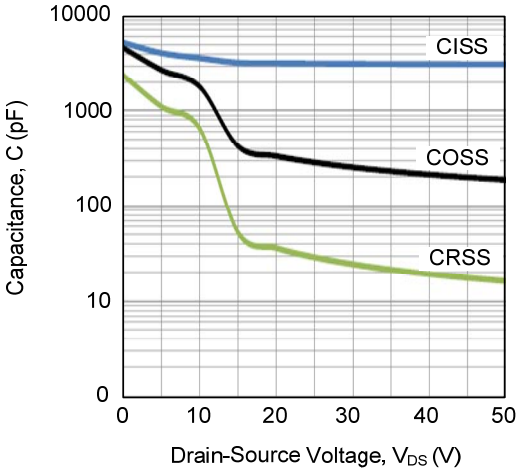
Drain-Source On-Resistance vs. Gate-Source Voltage



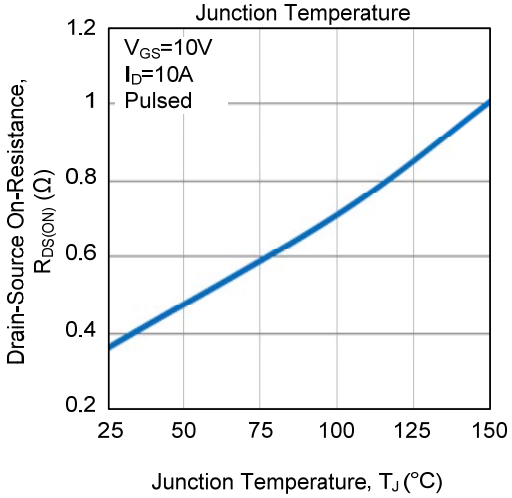
Gate Charge Characteristics



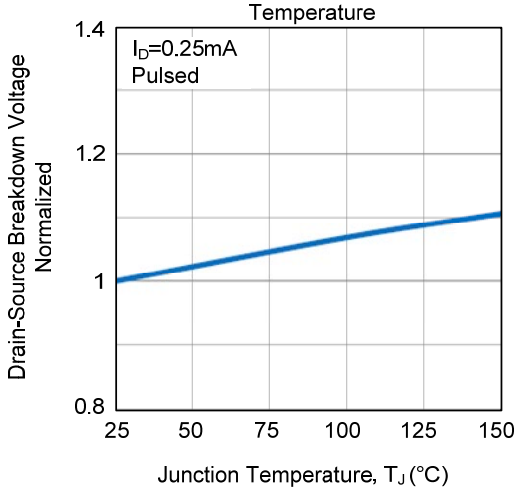
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

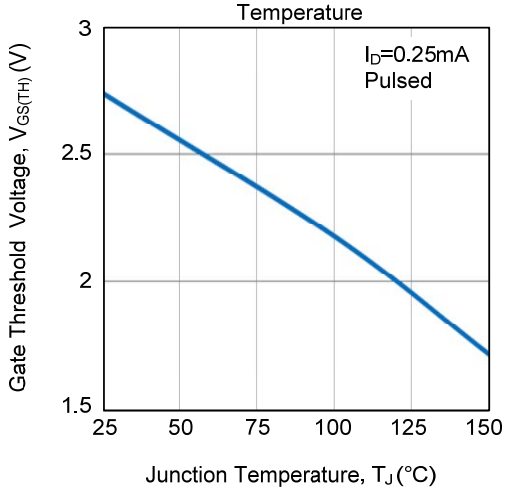


Breakdown Voltage vs. Junction Temperature

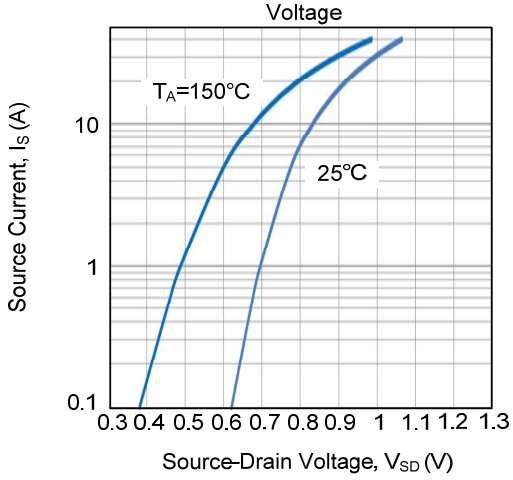


■ TYPICAL CHARACTERISTICS (Cont.)

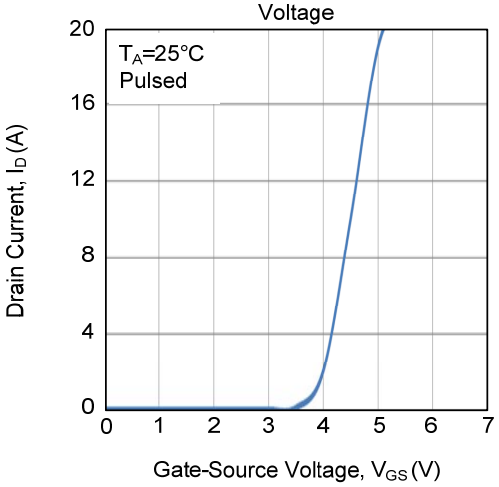
Gate Threshold Voltage vs. Junction Temperature



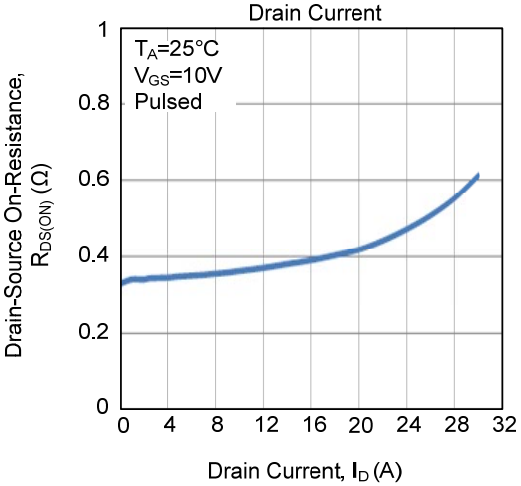
Source Current vs. Source-Drain Voltage



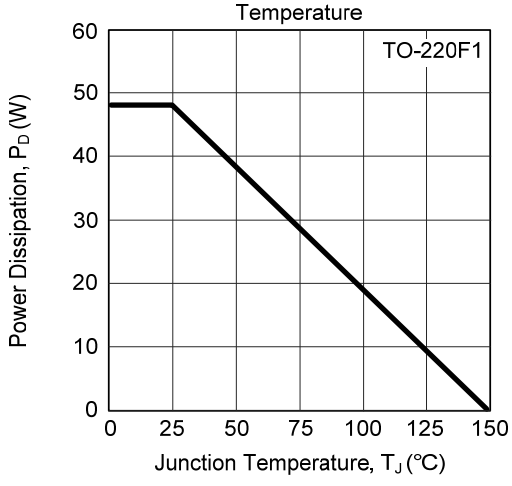
Drain Current vs. Gate-Source Voltage



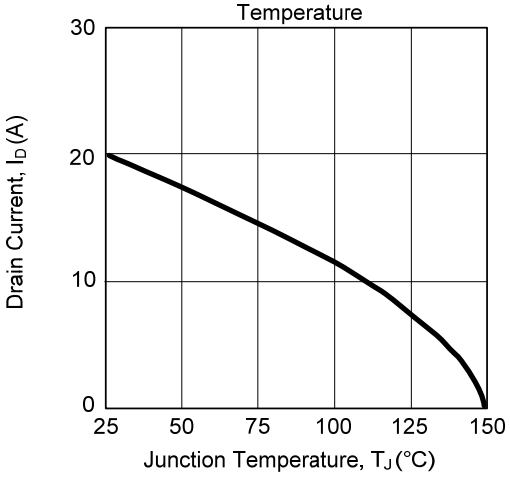
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)